



**MPS3392/FTSO3392**  
**MPS3393/FTSO3393**

NPN Small Signal General Purpose Amplifiers

T-29-23

- $V_{CE0}$  ... 25 V (Min)
- $h_{FE}$  ... 150-300 (MPS/FTSO3392), 90-180 (MPS/FTSO3393)  
 @ 2.0 mA
- Complements ... 2N4125, 2N4126

**PACKAGE**

MPS3392	TO-92
MPS3393	TO-92
FTSO3392	TO-236AA/AB
FTSO3393	TO-236AA/AB

**ABSOLUTE MAXIMUM RATINGS** (Note 1)

**Temperatures**

Storage Temperature	-55° to 150° C
Operating Junction Temperature	150° C

**Power Dissipation** (Notes 2 & 3)

Total Dissipation at	<b>MPS</b>	<b>FTSO</b>
25° C Ambient Temperature	0.625 W	0.350 W*
70° C Ambient Temperature	0.400 W	
25° C Case Temperature	1.0 W	

**Voltages & Currents**

$V_{CE0}$ Collector to Emitter Voltage (Note 4)	25 V
$V_{CB0}$ Collector to Base Voltage	25 V
$V_{EB0}$ Emitter to Base Voltage	5.0 V
$I_C$ Collector Current	100 mA

**ELECTRICAL CHARACTERISTICS** (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	3392		3393		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$BV_{CE0}$	Collector to Emitter Breakdown Voltage	25		25		V	$I_C = 1.0$ mA, $I_B = 0$
$I_{E0}$	Emitter Cutoff Current		100		100	nA	$V_{EB} = 5.0$ V, $I_C = 0$
$I_{C0}$	Collector Cutoff Current		100		100	nA	$V_{CB} = 18$ V, $I_E = 0$
$h_{FE}$	DC Current Gain (Note 5)	150	300	90	180		$I_C = 2.0$ mA, $V_{CE} = 4.5$ V
$C_{ob}$	Output Capacitance		3.5		3.5	pF	$V_{CB} = 10$ V, $I_E = 0$ , $f = 1.0$ MHz
$h_{fe}$	Small Signal Current Gain	150	500	90	400		$I_C = 2.0$ mA, $V_{CE} = 4.5$ V, $f = 1.0$ kHz

**NOTES:**

1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3. These ratings give a maximum junction temperature of 150° C and (TO-92) junction-to-case thermal resistance of 125° C/W (derating factor of 8.0 mW/° C), junction-to-ambient thermal resistance of 200° C/W (derating factor of 5.0 mW/° C); (TO-236) junction-to-ambient thermal resistance of 357° C/W (derating factor of 2.8 mW/° C).
4. Rating refers to a high current point where collector to emitter voltage is lowest.
5. Pulse conditions: length = 300  $\mu$ s, duty cycle = 1%
6. For product family characteristic curves, refer to Curve Set T144.



**MPS3702/FTSO3702**  
**MPS3703/FTSO3703**

PNP Small Signal General Purpose Amplifier

T-29-2B

- $V_{CE0}$  ... -30 V (Min) (MPS/FTSO3703)
- $h_{FE}$  ... 60-300 @ 50 mA (MPS/FTSO3702)
- $V_{CE(sat)}$  ... -0.25 V (Max) @ 50 mA
- Complements ... MPS/FTSO3704, MPS/FTSO3705

<b>PACKAGE</b>	
MPS3702	TO-92
MPS3703	TO-92
FTSO3702	TO-236AA/AB
FTSO3703	TO-236AA/AB

**ABSOLUTE MAXIMUM RATINGS (MPS3702, MPS3703) (Note 1)**

<b>Temperatures</b>	
Storage Temperature	-55° C to 150° C
Operating Junction Temperature	150° C

<b>Power Dissipation (Notes 2 &amp; 3)</b>		
Total Dissipation at	<b>MPS</b>	<b>FTSO</b>
25° C Ambient Temperature	0.625 W	0.350 W*
70° C Ambient Temperature	0.400 W	
25° C Case Temperature	1.0 W	

<b>Voltages &amp; Currents</b>		
	<b>3702</b>	<b>3703</b>
$V_{CE0}$ Collector to Emitter Voltage (Note 4)	-25 V	-30 V
$V_{CB0}$ Collector to Base Voltage	-40 V	-50 V
$V_{EB0}$ Emitter to Base Voltage	-5.0 V	-5.0 V
$I_c$ Collector Current	200 mA	200 mA

**ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)**

SYMBOL	CHARACTERISTIC	3702		3703		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$BV_{CE0}$	Collector to Emitter Breakdown Voltage (Note 5)	-25		-30		V	$I_c = 10 \text{ mA}, I_E = 0$
$BV_{CB0}$	Collector to Base Breakdown Voltage	-40		-50		V	$I_c = 100 \mu\text{A}, I_E = 0$
$BV_{EB0}$	Emitter to Base Breakdown Voltage	-5.0		-5.0		V	$I_E = 100 \mu\text{A}, I_c = 0$
$I_{CB0}$	Collector Cutoff Current		100		100	nA	$V_{CB} = -20 \text{ V}, I_E = 0$
$I_{EB0}$	Emitter Cutoff Current		100		100	nA	$V_{EB} = -3.0 \text{ V}, I_c = 0$

**NOTES:**

1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired
  2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
  3. These ratings give a maximum junction temperature of 150° C and (TO-92) junction-to-case thermal resistance of 125° C/W (derating factor of 8.0 mW/° C); junction-to-ambient thermal resistance of 200° C/W (derating factor of 5.0 mW/° C); (TO-236) junction-to-ambient thermal resistance of 357° C/W (derating factor of 2.8 mW/° C).
  4. Rating refers to a high current point where collector to emitter voltage is lowest
  5. Pulse conditions: length = 300  $\mu\text{s}$ ; duty cycle = 1%.
  6. For product family characteristic curves, refer to Curve Set T212.
- \* Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.

MPS3702/FTSO3702  
MPS3703/FTSO3703

T-29-23

**ELECTRICAL CHARACTERISTICS** (25°C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	3702		3703		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$h_{FE}$	DC Current Gain (Note 5)	60	300	30	150		$I_C = 50 \text{ mA}$ , $V_{CE} = -5.0 \text{ V}$
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Note 5)		-0.25		-0.25	V	$I_C = 50 \text{ mA}$ , $I_B = 5.0 \text{ mA}$
$V_{BE(ON)}$	Base to Emitter "On" Voltage (Note 5)	-0.6	-1.0	-0.6	-1.0	V	$I_C = 50 \text{ mA}$ , $V_{CE} = -5.0 \text{ V}$
$f_T$	Current Gain Bandwidth Product	100		100		MHz	$I_C = 50 \text{ mA}$ , $V_{CE} = -5.0 \text{ V}$ , $f = 20 \text{ MHz}$
$C_{ob}$	Output Capacitance		12		12	pF	$V_{CB} = -10 \text{ V}$ , $f = 1.0 \text{ MHz}$



**MPS3704/FTSO3704**  
**MPS3705/FTSO3705**  
 NPN Small Signal General Purpose Amplifiers

T-29-23

- $V_{CE0} \dots 30 \text{ V (Min)}$
- $h_{FE} \dots 100\text{-}300 \text{ @ } 50 \text{ mA (MPS/FTSO3704)}$
- $V_{CE(sat)} \dots -0.6 \text{ V (Max) @ } 100 \text{ mA (MPS/FTSO3704)}$
- Complements ... MPS/FTSO3702, MPS/FTSO3703

PACKAGE	
MPS3704	TO-92
MPS3705	TO-92
FTSO3704	TO-236AA/AB
FTSO3705	TO-236AA/AB

**ABSOLUTE MAXIMUM RATINGS (Note 1)**

Temperatures	
Storage Temperature	-55° C to 150° C
Operating Junction Temperature	150° C

Power Dissipation (Notes 2 & 3)		
Total Dissipation at	MPS	FTSO
25° C Ambient Temperature	0.625 W	0.350 W*
70° C Ambient Temperature	0.400 W	
25° C Case Temperature	1.0 W	

Voltages & Currents	
$V_{CE0}$ Collector to Emitter Voltage (Note 4)	30 V
$V_{CBO}$ Collector to Base Voltage	50 V
$V_{EBO}$ Emitter to Base Voltage	5.0 V
$I_C$ Collector Current	600 mA

**ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)**

SYMBOL	CHARACTERISTIC	3704		3705		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$BV_{CE0}$	Collector to Emitter Breakdown Voltage (Note 5)	30		30		V	$I_C = 10 \text{ mA}, I_E = 0$
$BV_{CBO}$	Collector to Base Breakdown Voltage	50		50		V	$I_C = 100 \mu\text{A}, I_E = 0$
$BV_{EBO}$	Emitter to Base Breakdown Voltage	5.0		5.0		V	$I_E = 100 \mu\text{A}, I_C = 0$
$I_{CBO}$	Collector Cutoff Current		100		100	nA	$V_{CB} = 20 \text{ V}, I_E = 0$
$I_{EBO}$	Emitter Cutoff Current		100		100	nA	$V_{EB} = 3.0 \text{ V}, I_C = 0$
$h_{FE}$	DC Current Gain (Note 5)	100	300	50	150		$I_C = 50 \text{ mA}, V_{CE} = 2.0 \text{ V}$

- NOTES:**
1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
  2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
  3. These ratings give a maximum junction temperature of 150° C and (TO-92) junction-to-case thermal resistance of 125° C/W (derating factor of 8.0 mW/° C); junction-to-ambient thermal resistance of 200° C/W (derating factor of 5.0 mW/° C); (TO-236) junction-to-ambient thermal resistance of 357° C/W (derating factor of 2.8 mW/° C).
  4. Rating refers to a high current point where collector to emitter voltage is lowest.
  5. Pulse conditions: length = 300 μs; duty cycle = 1%
  6. For product family characteristic curves, refer to Curve Set T145.
- \* Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.

MPS3704/FTSO3704  
MPS3705/FTSO3705

T-29-23

**ELECTRICAL CHARACTERISTICS** (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	3704		3705		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Note 5)		0.6		0.8	V	$I_C = 100 \text{ mA}$ , $I_B = 5.0 \text{ mA}$
$V_{BE(ON)}$	Base to Emitter "On" Voltage (Note 5)	0.5	1.0	0.5	1.0	V	$I_C = 100 \text{ mA}$ , $V_{CE} = 2.0 \text{ V}$
$f_T$	Current Gain Bandwidth Product	100		100		MHz	$I_C = 50 \text{ mA}$ , $V_{CE} = 2.0 \text{ V}$ , $f = 20 \text{ MHz}$
$C_{ob}$	Output Capacitance		12		12	pF	$V_{CB} = 10 \text{ V}$ , $I_E = 0$ , $f = 1.0 \text{ MHz}$



## MPS5172/FTSO5172

NPN Small Signal General Purpose Amplifier

T-29-23

- $h_{FE} \dots 100-500 @ I_C = 10 \text{ mA}$
- $V_{CE(sat)} \dots 0.25 \text{ V (Max)} @ I_C = 10 \text{ mA}$
- Complements ... 2N4126, FTSO4126

PACKAGE	
MPS5172	TO-92
FTSO5172	TO-236AA/AB

## ABSOLUTE MAXIMUM RATINGS (Note 1)

## Temperatures

Storage Temperature	-55° C to 150° C
Operating Junction Temperature	150° C

## Power Dissipation (Notes 2 &amp; 3)

Total Dissipation at	MPS	FTSO
25° C Ambient Temperature	0.625 W	0.350 W*
70° C Ambient Temperature	0.400 W	
25° C Case Temperature	1.0 W	

## Voltages &amp; Currents

$V_{CEO}$ Collector to Emitter Voltage (Note 4)	25 V
$V_{CBO}$ Collector to Base Voltage	25 V
$V_{EBO}$ Emitter to Base Voltage	5.0 V
$I_C$ Collector Current	100 mA

## ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
$BV_{CEO}$	Collector to Emitter Breakdown Voltage	25		V	$I_C = 10 \text{ mA}, I_B = 0$
$I_{CES}$	Collector Cutoff Current		100	nA	$V_{CE} = 25 \text{ V}, V_{BE} = 0$
$I_{CBO}$	Collector Cutoff Current		100 10	nA $\mu\text{A}$	$V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 25 \text{ V}, I_E = 0.1, T_A = 100^\circ \text{C}$
$I_{EBO}$	Emitter Cutoff Current		100	nA	$V_{BE} = 5.0 \text{ V}, I_C = 0$
$h_{FE}$	DC Current Gain (Note 5)	100	500		$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Note 5)		0.25	V	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$
$V_{BE(ON)}$	Base to Emitter "On" Voltage	0.5	1.2	V	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$
$C_{cb}$	Collector to Base Capacitance	1.6	10	pF	$V_{CB} = 0, I_E = 0, f = 1.0 \text{ MHz}$
$h_{fe}$	Small Signal Current Gain	100	750		$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$

## NOTES:

1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
  2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
  3. These ratings give a maximum junction temperature of 150° C and (TO-92) junction-to-case thermal resistance of 125° C/W (derating factor of 80 mW/° C); junction-to-ambient thermal resistance of 200° C/W (derating factor of 5.0 mW/° C); (TO-236) junction-to-ambient thermal resistance of 357° C/W (derating factor of 2.8 mW/° C).
  4. Rating refers to a high current point where collector to emitter voltage is lowest.
  5. Pulse conditions: length = 300  $\mu\text{s}$ ; duty cycle = 1%.
  6. For product family characteristic curves, refer to Curve Set T144.
- \* Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.



**MPS6514/FTSO6514**  
**MPS6515/FTSO6515**  
 NPN Small Signal General  
 Purpose Amplifiers

T-29.23

- $V_{CE0} \dots 25 \text{ V (Min)}$
- $h_{FE} \dots 150\text{-}300 \text{ (MPS/FTSO6514)}, 250\text{-}500 \text{ (MPS/FTSO6515)}$   
 @ 2.0 mA
- $h_{FE} \dots 90 \text{ (Min) (MPS/FTSO6514)}, 150 \text{ (Min)}$   
 (MPS/FTSO6515) @ 100 mA

<b>PACKAGE</b>	
MPS6514	TO-92
MPS6515	TO-92
FTSO6514	TO-236AA/AB
FTSO6515	TO-236AA/AB

**ABSOLUTE MAXIMUM RATINGS (Note 1)**

**Temperatures**

Storage Temperature	-55°C to 150°C
Operating Junction Temperature	150°C

**Power Dissipation (Notes 2 & 3)**

Total Dissipation at	<b>MPS</b>	<b>FTSO</b>
25°C Ambient Temperature	0.625 W	0.350 W*
70°C Ambient Temperature	0.400 W	
25°C Case Temperature	1.0 W	

**Voltages & Currents**

$V_{CE0}$ Collector to Emitter Voltage (Note 4)	25 V
$V_{CBO}$ Collector to Base Voltage	40 V
$V_{EBO}$ Emitter to Base Voltage	4.0 V
$I_C$ Collector Current	100 mA

**ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted) (Note 6)**

SYMBOL	CHARACTERISTIC	6514		6515		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$BV_{CE0}$	Collector to Emitter Breakdown Voltage	30		30		V	$I_C = 0.5 \text{ mA}, I_B = 0$
$BV_{EBO}$	Emitter to Base Breakdown Voltage	4.0		4.0		V	$I_E = 100 \mu\text{A}, I_C = 0$
$I_{CBO}$	Collector Cutoff Current		50 1.0		50 1.0	nA $\mu\text{A}$	$V_{CB} = 30 \text{ V}, I_E = 0$ $V_{CB} = 30 \text{ V}, I_E = 0, T_A = 60^\circ\text{C}$
$h_{FE}$	DC Current Gain (Note 5)	150 90	300	250 150	500		$I_C = 2.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 10 \text{ V}$
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage (Note 5)		0.5		0.5	V	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$
$C_{ob}$	Output Capacitance		3.5		3.5	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 100 \text{ kHz}$

**NOTES:**

1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3. These ratings give a maximum junction temperature of 150°C and (TO-92) junction-to-case thermal resistance of 125°C/W (derating factor of 8.0 mW/°C), junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 357°C/W (derating factor of 2.8 mW/°C).
4. Rating refers to a high current point where collector to emitter voltage is lowest.
5. Pulse conditions: length = 300  $\mu\text{s}$ ; duty cycle = 1%.
6. For product family characteristic curves, refer to Curve Set T144 for MPS6514 & T-155 for MPS6515
- \* Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.



# MPS6518/FTSO6518

PNP Small Signal General Purpose Amplifier

T-29-23

- $V_{CE0} \dots 40 \text{ V (Min)}$
- $h_{FE} \dots 150\text{-}300 @ 2.0 \text{ mA, } 90 \text{ (Min) @ } 100 \text{ mA}$

**PACKAGE**  
 MPS6518 TO-92  
 FTSO6518 TO-236AA/AB

**ABSOLUTE MAXIMUM RATINGS** (Note 1)**Temperatures**

Storage Temperature  $-55^\circ \text{C}$  to  $150^\circ \text{C}$   
 Operating Junction Temperature  $150^\circ \text{C}$

**Power Dissipation** (Notes 2 & 3)

Total Dissipation at	MPS	FTSO
$25^\circ \text{C}$ Ambient Temperature	0.625 W	0.350 W*
$70^\circ \text{C}$ Ambient Temperature	0.400 W	
$25^\circ \text{C}$ Case Temperature	1.0 W	

**Voltages & Currents**

$V_{CE0}$ Collector to Emitter Voltage (Note 4)	$-40 \text{ V}$
$V_{CB0}$ Collector to Base Voltage	$-40 \text{ V}$
$V_{EB0}$ Emitter to Base Voltage	$-4.0 \text{ V}$
$I_C$ Collector Current	$100 \text{ mA}$

**ELECTRICAL CHARACTERISTICS** ( $25^\circ \text{C}$  Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
$BV_{CE0}$	Collector to Emitter Breakdown Voltage	$-40$		V	$I_C = 0.5 \text{ mA, } I_B = 0$
$BV_{EB0}$	Emitter to Base Breakdown Voltage	$-4.0$		V	$I_E = 10 \mu\text{A, } I_C = 0$
$I_{CBO}$	Collector Cutoff Current		50 1.0	nA $\mu\text{A}$	$V_{CB} = -30 \text{ V, } I_E = 0$ $V_{CB} = -30 \text{ V, } I_E = 0, T_A = 60^\circ \text{C}$
$h_{FE}$	DC Current Gain (Note 5)	150 90	300		$I_C = 2.0 \text{ mA, } V_{CE} = -10 \text{ V}$ $I_C = 100 \text{ mA, } V_{CE} = -10 \text{ V}$
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Note 5)		$-0.5$	V	$I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA}$
$C_{ob}$	Output Capacitance		4.0	pF	$V_{CB} = -10 \text{ V, } I_E = 0, f = 100 \text{ kHz}$

**NOTES:**

- These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
  - These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
  - These ratings give a maximum junction temperature of  $150^\circ \text{C}$  and (TO-92) junction-to-case thermal resistance of  $125^\circ \text{C/W}$  (derating factor of  $8.0 \text{ mW}^\circ \text{C}$ ); junction-to-ambient thermal resistance of  $200^\circ \text{C/W}$  (derating factor of  $5.0 \text{ mW}^\circ \text{C}$ ); (TO-236) junction-to-ambient thermal resistance of  $357^\circ \text{C/W}$  (derating factor of  $2.8 \text{ mW}^\circ \text{C}$ ).
  - Rating refers to a high current point where collector to emitter voltage is lowest.
  - Pulse conditions: length =  $300 \mu\text{s}$ ; duty cycle = 1%
  - For product family characteristic curves, refer to Curve Set T215.
- \* Package mounted on 99.5% alumina  $8 \text{ mm} \times 8 \text{ mm} \times 0.6 \text{ mm}$ .



**FAIRCHILD**

A Schlumberger Company

**MPS6520/FTSO6520**  
**MPS6521/FTSO6521**NPN Small Signal General  
Purpose Amplifiers

T-29-23

- $V_{CE0}$  ... 25 V (Min)
- $h_{FE}$  ... 100 (Min) (MPS/FTSO6520), 150 (Min) (MPS/FTSO6521) @ 100  $\mu$ A
- $h_{FE}$  ... 200-400 (MPS/FTSO6520), 300-600 (MPS/FTSO6521) @ 2.0 mA
- NF ... 3.0 dB (Max) @  $I_C = 10 \mu$ A, Wide Band

**PACKAGE**

MPS6520	TO-92
MPS6521	TO-92
FTSO6520	TO-236AA/AB
FTSO6521	TO-236AA/AB

**ABSOLUTE MAXIMUM RATINGS** (Note 1)**Temperatures**

Storage Temperature	-55° C to 150° C
Operating Junction Temperature	150° C

**Power Dissipation** (Notes 2 & 3)

Total Dissipation at	<b>MPS</b>	<b>FTSO</b>
25° C Ambient Temperature	0.625 W	0.350 W*
70° C Ambient Temperature	0.400 W	
25° C Case Temperature	1.0 W	

**Voltages & Currents**

$V_{CE0}$ Collector to Emitter Voltage	25 V
(Note 4)	
$V_{CBO}$ Collector to Base Voltage	40 V
$V_{EBO}$ Emitter to Base Voltage	4.0 V
$I_C$ Collector Current	100 mA

**ELECTRICAL CHARACTERISTICS** (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	6520		6521		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$BV_{CE0}$	Collector to Emitter Breakdown Voltage	25		25		V	$I_C = 0.5 \text{ mA}$ , $I_B = 0$
$BV_{EBO}$	Emitter to Base Breakdown Voltage	4.0		4.0		V	$I_E = 10 \mu\text{A}$ , $I_C = 0$
$I_{CBO}$	Collector Cutoff Current		50 1.0		50 1.0	nA $\mu\text{A}$	$V_{CB} = 30 \text{ V}$ , $I_E = 0$ $V_{CB} = 30 \text{ V}$ , $I_E = 0$ , $T_A = 60^\circ \text{ C}$

**NOTES:**

- These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- These ratings give a maximum junction temperature of 150° C and (TO-92) junction-to-case thermal resistance of 125° C/W (derating factor of 8.0 mW/°C); junction-to-ambient thermal resistance of 200° C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 357° C/W (derating factor of 2.8 mW/°C).
- Rating refers to a high current point where collector to emitter voltage is lowest.
- Pulse conditions: length = 300  $\mu$ s; duty cycle = 1%.
- For product family characteristic curves, refer to Curve Set T144.
- \* Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.

MPS6520/FTSO6520  
MPS6521/FTSO6521

T-29.23

**ELECTRICAL CHARACTERISTICS** (25°C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	6520		6521		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$h_{FE}$	DC Current Gain	100 200	400	150 300	600		$I_C = 100 \mu A, V_{CE} = 10 V$ $I_C = 2.0 mA, V_{CE} = 10 V$
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Note 5)		0.5		0.5	V	$I_C = 50 mA, I_B = 5.0 mA$
$C_{ob}$	Output Capacitance		3.5		3.5	pF	$V_{CE} = 10 V, I_E = 0, f = 100 kHz$
NF	Noise Figure		3.0		3.0	dB	$V_{CE} = 5.0 V, I_C = 10 \mu A,$ $R_g = 10 k\Omega,$ Power Bandwidth $\pm 15.7 kHz,$ 3.0 dB pts @ 10 Hz & 10 kHz



A Schlumberger Company

# MPS6535M T-29-23

PNP Small Signal General Purpose Amplifier

- $P_D$  625 mW @  $T_A = 25^\circ\text{C}$
- $V_{CE0}$  ... -30 V (Min)
- $h_{FE}$  ... 30 (Min) @ 100 mA

**PACKAGE**  
MPS6535M TO-92

**ABSOLUTE MAXIMUM RATINGS** (Note 1)**Temperatures**

Storage Temperature  $-55^\circ\text{C}$  to  $150^\circ\text{C}$   
Operating Junction Temperature  $150^\circ\text{C}$

**Power Dissipation** (Notes 2 & 3)

Total Dissipation at  
25° C Ambient Temperature 0.625 W  
70° C Ambient Temperature 0.400 W  
25° C Case Temperature 1.0 W

**Voltages & Currents**

$V_{CE0}$  Collector to Emitter Voltage -30 V  
(Note 4)  
 $V_{CBO}$  Collector to Base Voltage -30 V  
 $V_{EBO}$  Emitter to Base Voltage -4.0 V  
 $I_C$  Collector Current 600 mA

**ELECTRICAL CHARACTERISTICS** (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
$BV_{CE0}$	Collector to Emitter Breakdown Voltage	-30		V	$I_C = 10\text{ mA}$ , $I_E = 0$
$BV_{CBO}$	Collector to Base Breakdown Voltage	-30		V	$I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$
$BV_{EBO}$	Emitter to Base Breakdown Voltage	-4.0		V	$I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$
$I_{CBO}$	Collector Cutoff Current		100 5.0	nA $\mu\text{A}$	$V_{CB} = -20\text{ V}$ , $I_E = 0$ $V_{CB} = -20\text{ V}$ , $I_E = 0$ , $T_A = 60^\circ\text{C}$
$h_{FE}$	DC Current Gain (Note 5)	30			$I_C = 100\text{ mA}$ , $V_{CE} = -1.0\text{ V}$
$V_{CE(sat)}$	Collector Saturation Voltage (Note 5)		-0.5	V	$I_C = 100\text{ mA}$ , $I_B = 10\text{ mA}$
$V_{BE(sat)}$	Base Saturation Voltage (Note 5)		-1.2	V	$I_C = 100\text{ mA}$ , $I_B = 10\text{ mA}$
$C_{ob}$	Output Capacitance		8.0	pF	$V_{CB} = -10\text{ V}$ , $I_E = 0$ , $f = 100\text{ kHz}$

**NOTES:**

1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3. These ratings give a maximum junction temperature of  $150^\circ\text{C}$  and (TO-92) junction-to-case thermal resistance of  $125^\circ\text{C/W}$  (derating factor of 8.0 mW/ $^\circ\text{C}$ ); junction-to-ambient thermal resistance of  $200^\circ\text{C/W}$  (derating factor of 5.0 mW/ $^\circ\text{C}$ ).
4. Rating refers to a high current point where collector to emitter voltage is lowest.
5. Pulse conditions: length = 300  $\mu\text{s}$ ; duty cycle = 2%.
6. For product family characteristic curves, refer to Curve Set T202.



**MPS6560/FTSO6560**  
**MPS6561/FTSO6561**  
**MPS6562/FTSO6562**  
 NPN-PNP Small Signal General  
 Purpose Complementary Amplifiers

T-29-23

- $V_{CE0}$  ... **MPS/FTSO6560/2),**  
**20 V (MPS/FTSO6561)**
- $h_{FE}$  ... **50-200 @ 500 mA (MPS/FTSO6560/2),**  
**@ 350 mA (MPS/FTSO6561)**
- $V_{CE(sat)}$  ... **0.5 V (Max) @ 500 mA (MPS/FTSO6560/2),**  
**@ 350 mA (MPS/FTSO6561)**
- Complements ... **MPS/FTSO6560, MPS/FTSO6561 (NPN);**  
**MPS/FTSO6562 (PNP)**

PACKAGE	
MPS6560	TO-92
MPS6561	TO-92
MPS6562	TO-92
FTSO6560	TO-236AA/AB
FTSO6561	TO-236AA/AB
FTSO6562	TO-236AA/AB

**ABSOLUTE MAXIMUM RATINGS** (Note 1)

Temperatures	
Storage Temperature	-55° C to 150° C
Operating Junction Temperature	150° C

Power Dissipation (Notes 2 & 3)	MPS	FTSO
Total Dissipation at		
25° C Ambient Temperature	0.625 W	0.350 W*
70° C Ambient Temperature	0.400 W	
25° C Case Temperature	1.0 W	

Voltages & Currents	6560/62	6561
$V_{CE0}$ Collector to Emitter Voltage (Note 4)	25 V	20 V
$V_{CBO}$ Collector to Base Voltage	25 V	20 V
$V_{EBO}$ Emitter to Base Voltage	4.0 V	4.0 V
$I_C$ Collector Current	600 mA	600 mA

**ELECTRICAL CHARACTERISTICS** (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	6560/62		6561		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$BV_{EBO}$	Emitter to Base Breakdown Voltage	5.0		-5.0		V	$I_E = 100 \mu A, I_C = 0$
$I_{CEO}$	Collector Cutoff Current		100		100	nA	$V_{CE} = 25 V, I_B = 0$ $V_{CE} = 20 V, I_B = 0$
$I_{CBO}$	Collector Cutoff Current		100		100	nA	$V_{CB} = 20 V, I_E = 0$
$I_{EBO}$	Emitter Cutoff Current		100		100	nA	$V_{EB} = 4.0 V, I_C = 0$

**NOTES:**

1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
  2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
  3. These ratings give a maximum junction temperature of 150° C and (TO-92) junction-to-case thermal resistance of 125° C/W (derating factor of 8.0 mW/° C), junction-to-ambient thermal resistance of 200° C/W (derating factor of 50 mW/° C); (TO-236) junction-to-ambient thermal resistance of 357° C/W (derating factor of 2.8 mW/° C).
  4. Rating refers to a high current point where collector to emitter voltage is lowest.
  5. Pulse conditions: length = 300  $\mu s$ ; duty cycle = 1%.
  6. For product family characteristic curves, refer to Curve Set T124 for MPS6560, MPS6561 & T12 for MPS6562.
- \* Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.

MPS6560/FTSO6560 T-29.23  
 MPS6561/FTSO6561  
 MPS6562/FTSO6562

**ELECTRICAL CHARACTERISTICS** (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	6560/62		6561		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$h_{FE}$	DC Current Gain (Note 5)	35 50 50	200	35 50 50	200		$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 350 \text{ mA}, V_{CE} = 1.0 \text{ V}$
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Note 5)		0.5		-0.5	V V	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ $I_C = 350 \text{ mA}, I_B = 35 \text{ mA}$
$V_{BE(on)}$	Base to Emitter "On" Voltage (Note 5)		1.2		-1.2	V V	$I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 350 \text{ mA}, V_{CE} = 1.0 \text{ V}$
$f_T$	Current Gain Bandwidth Product	60		60		MHz	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 30 \text{ MHz}$
$C_{ob}$	Output Capacitance		30		30	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 100 \text{ kHz}$



# MPS6571/FTSO6571

## NPN Low Level High Gain Amplifier

T-29-23

- $V_{CE0} \dots -20 \text{ V (Min)}$
- $h_{FE} \dots 250-1000 @ 100 \mu\text{A}$

**PACKAGE**MPS6571  
FTSO6571

TO-92

TO236AA/AB

**ABSOLUTE MAXIMUM RATINGS** (Note 1)**Temperatures**

Storage Temperature  $-55^\circ\text{C}$  to  $150^\circ\text{C}$   
 Operating Junction Temperature  $150^\circ\text{C}$

**Power Dissipation** (Notes 2 & 3)

Total Dissipation at	MPS	FTSO
25°C Ambient Temperature	0.625 W	0.350 W*
70°C Ambient Temperature	0.400 W	
25°C Case Temperature	1.0 W	

**Voltages & Currents**

$V_{CE0}$ Collector to Emitter Voltage (Note 4)	20 V
$V_{CBO}$ Collector to Base Voltage	20 V
$V_{EBO}$ Emitter to Base Voltage	3.0 V
$I_C$ Collector Current (Continuous)	50 mA

**ELECTRICAL CHARACTERISTICS** (25°C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
$BV_{CE0}$	Collector to Emitter Breakdown Voltage	20		V	$I_C = 1.0 \text{ mA}$ , $I_B = 0$
$BV_{CBO}$	Collector to Base Breakdown Voltage	25		V	$I_C = 100 \mu\text{A}$ , $I_E = 0$
$I_{CBO}$	Collector Cutoff Current		50	nA	$V_{CB} = 20 \text{ V}$ , $I_E = 0$
$I_{EBO}$	Emitter Cutoff Current		50	nA	$V_{EB(OFF)} = 3.0 \text{ V}$ , $I_C = 0$
$h_{FE}$	DC Current Gain (Note 5)	250	1000		$I_C = 100 \mu\text{A}$ , $V_{CE} = 5.0 \text{ V}$
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Note 5)		0.5	V	$I_C = 10 \text{ mA}$ , $I_B = 1.0 \text{ mA}$
$V_{BE(ON)}$	Base to Emitter "On" Voltage (Note 5)		0.8	V	$I_C = 10 \text{ mA}$ , $V_{CE} = 5.0 \text{ V}$
$f_T$	Current Gain Bandwidth Product	50		MHz	$I_C = 500 \mu\text{A}$ , $V_{CE} = 5.0 \text{ V}$ , $f = 20 \text{ MHz}$
$C_{ob}$	Output Capacitance		4.5	pF	$V_{CB} = 5.0 \text{ V}$ , $I_E = 0$ , $f = 100 \text{ kHz}$

**NOTES:**

- These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
  - These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
  - These ratings give a maximum junction temperature of  $150^\circ\text{C}$  and (TO-92) junction-to-case thermal resistance of  $125^\circ\text{C/W}$  (derating factor of  $8.0 \text{ mW}^\circ\text{C}$ ); junction-to-ambient thermal resistance of  $200^\circ\text{C/W}$  (derating factor of  $5.0 \text{ mW}^\circ\text{C}$ ); (TO-236) junction-to-ambient thermal resistance of  $357^\circ\text{C/W}$  (derating factor of  $2.8 \text{ mW}^\circ\text{C}$ ).
  - Rating refers to a high current point where collector to emitter voltage is lowest.
  - Pulse conditions: length =  $300 \mu\text{s}$ ; duty cycle = 1%.
  - For product family characteristic curves, refer to Curve Set T144.
- \* Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.



**MPSA05/FTSOA05**  
**MPSA06/FTSOA06**  
 NPN Small Signal General  
 Purpose Amplifiers

T-29-23

- $V_{CE0}$  ... 60 V (Min) (MPS/FTSOA05), 80 V (Min) (MPS/FTSOA06)
- $h_{FE}$  ... 50 (Min) @ 10 mA and 100 mA
- $V_{CE(sat)}$  ... 0.25 V (Max) @ 100 mA
- Complements ... MPS/FTSOA55, MPS/FTSOA56, (PNP)

<b>PACKAGE</b>	
MPSA05	TO-92
MPSA06	TO-92
FTSOA05	TO-236AA/AB
FTSOA06	TO-236AA/AB

**ABSOLUTE MAXIMUM RATINGS (Note 1)**

<b>Temperatures</b>	
Storage Temperature	-55° C to 150° C
Operating Junction Temperature	150° C

<b>Power Dissipation (Notes 2 &amp; 3)</b>		
Total Dissipation at	<b>MPS</b>	<b>FTSO</b>
25° C Ambient Temperature	0.625 W	0.350 W*
70° C Ambient Temperature	0.400 W	
25° C Case Temperature	1.0 W	

<b>Voltages &amp; Currents</b>		
$V_{CE0}$ Collector to Emitter Voltage (Note 4)	<b>A05</b> 60 V	<b>A06</b> 80 V
$V_{CB0}$ Collector to Base Voltage	60 V	80 V
$V_{EB0}$ Emitter to Base Voltage	4.0 V	4.0 V
$I_c$ Collector Current	500 mA	500 mA

**ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)**

SYMBOL	CHARACTERISTIC	A05		A06		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$BV_{CE0}$	Collector to Emitter Breakdown Voltage	60		80		V	$I_c = 1.0 \text{ mA}, I_E = 0$
$BV_{EB0}$	Emitter to Base Breakdown Voltage	4.0		4.0		V	$I_E = 100 \text{ } \mu\text{A}, I_c = 0$
$I_{CB0}$	Collector Cutoff Current		100		100	nA	$V_{CB} = 60 \text{ V}, I_E = 0$ $V_{CB} = 80 \text{ V}, I_E = 0$

**NOTES:**

1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
  2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
  3. These ratings give a maximum junction temperature of 150° C and (TO-92) junction-to-case thermal resistance of 125° C/W (derating factor of 8.0 mW/° C); junction-to-ambient thermal resistance of 200° C/W (derating factor of 5.0 mW/° C); (TO-236) junction-to-ambient thermal resistance of 357° C/W (derating factor of 2.8 mW/° C).
  4. Rating refers to a high current point where collector to emitter voltage is lowest.
  5. Pulse conditions: length = 300  $\mu$ s; duty cycle = 1%.
  6. For product family characteristic curves, refer to Curve Set T149.
- \* Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.

MPSA05/FTSOA05  
MPSA06/FTSOA06

7-29-23

**ELECTRICAL CHARACTERISTICS** (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	A05		A06		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
$h_{FE}$	DC Current Gain (Note 5)	50		50			$I_C = 100 \text{ mA}$ , $V_{CE} = 1.0 \text{ V}$ $I_C = 10 \text{ mA}$ , $V_{CE} = 1.0 \text{ V}$
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Note 5)		0.25		0.25	V	$I_C = 100 \text{ mA}$ , $I_B = 10 \text{ mA}$
$V_{BE(on)}$	Base to Emitter "On" Voltage		1.2		1.2	V	$I_C = 100 \text{ mA}$ , $V_{CE} = 1.0 \text{ V}$
$f_T$	Current Gain Bandwidth Product	50		50		MHz	$I_C = 100 \text{ mA}$ , $V_{CE} = 1.0 \text{ V}$ , $f = 100 \text{ MHz}$